

CLAIMS

1. A method of forming an electrical connection structure, the method comprising:
 - providing a first substrate having a first surface;
 - forming a cavity on the first surface;
 - forming an inner wall defining a via extending from the cavity;
 - forming an interconnect structure in the via so that at least a portion of the interconnect structure protrudes into the cavity, the interconnect structure being any one structure selected from a group consisting of a pillar and a wire;
 - providing a second substrate having a second surface facing the first surface; and
 - forming a connection element on the second surface;
 - wherein at least a portion of the connection element is received in the cavity so that the connection element is in electrical connection with the interconnect structure; and
 - wherein the cavity is a hemispherical cavity.
2. The method according to claim 1,
 - wherein the cavity is formed after forming the interconnect structure.
3. The method according to claim 1, further comprising:
 - forming an interconnect finishing layer on the portion of the interconnect structure protruding into the cavity by using one of electroless plating and immersion plating.
4. The method according to claim 1, further comprising:
 - forming a cavity finishing layer on at least a portion of the first surface defining the cavity by using at least one of sputtering and plating.